IN THE CLAIMS

This listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Original) A heat treatment method for heat treating a silicon wafer in a treatment furnace, comprising supporting a silicon wafer by three support positions within a region where a radial distance from a center is defined by 85 to 99.5% of a wafer radius.

2. (Original) A heat treatment method for a silicon wafer utilizing a three-points supporting device comprising:

three support arms protruding from a support frame towards a center so as to form an intervening spacing with each other; and

support projections projecting upwards from each support arm, on which a silicon wafer is mounted and heat-treated in a heat treatment furnace,

wherein, when all the support projections are positioned on a same circle, all the support projections are positioned within a region where a radial distance from the center is defined by 85 to 99.5% of the wafer radius, and the support arms are arranged so as to form an angle of 120° with each other about the center point.

3. (Currently Amended) A heat treatment jig for a silicon wafer, comprising:

a support ~~flame~~ frame;

three support arms protruding from the support frame towards a center so as to form an intervening spacing with each other; and

support projections projecting upwards from each support arm,

wherein the support arms are arranged so as to form an angle of 120° with each other about the center, and

positions of all the support projections can be preset so that they are positioned around a same circle about the center point, within a region where a radial distance from the center is defined by 85 to 99.5% of the wafer radius.

4. (Original) A heat treatment jig of a silicon wafer according to Claim 3, wherein the support projections are fixed to the support arms so that fixing positions can be preset.

5. (Currently Amended) A wafer heat treated by the heat treatment method according to ~~Claims 1 or 2~~ Claim 1.

6. (New) A wafer heat treated by the heat treatment method according to 2.